

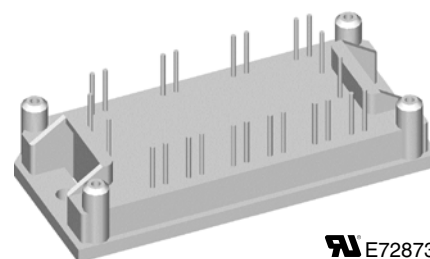
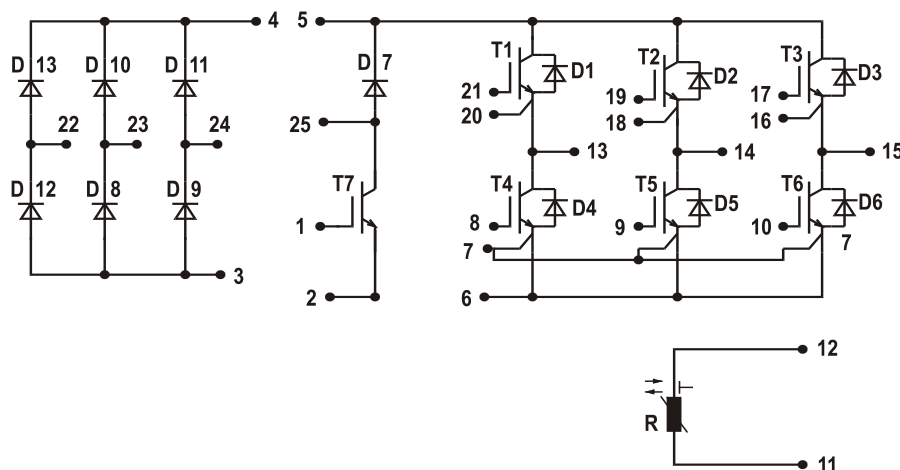
Converter - Brake - Inverter Module (CBI 1) **NPT IGBT**

Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{DAVM25} = 130 \text{ A}$	$I_{C25} = 19 \text{ A}$	$I_{C25} = 30 \text{ A}$
$I_{FSM} = 320 \text{ A}$	$V_{CE(sat)} = 2.9 \text{ V}$	$V_{CE(sat)} = 3 \text{ V}$

Preliminary data

Part name (Marking on product)

MUBW30-12A6K



 E72873

Pin configuration see outlines.

Features:

- High level of integration - only one power semiconductor module required for the whole drive
- Inverter with NPT IGBTs
- low saturation voltage
- positive temperature coefficient
- fast switching
- short tail current
- Epitaxial free wheeling diodes with hiperfast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

Application:

- AC motor drives with
- Input from single or three phase grid
 - Three phase synchronous or asynchronous motor
 - Electric braking operation

Package:

- UL registered
- Industry standard E1-pack

Output Inverter T1 - T6

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$ to 150°C			1200		V
V_{GES}	max. DC gate voltage	continuous			± 20		V
V_{GEM}	max. transient collector gate voltage	transient			± 30		V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			30		A
I_{C80}		$T_C = 80^{\circ}\text{C}$			21		A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			130		W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 30\text{ A}; V_{GE} = 15\text{ V}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	3.0 3.4	3.8	V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.6\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	4.5		6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.5	1	mA mA
I_{GES}	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$				200	nA
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		1000			pF
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 17.5\text{ A}$		70			nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 15\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$	100			ns
t_r	current rise time			80			ns
$t_{d(off)}$	turn-off delay time			500			ns
t_f	current fall time			70			ns
E_{on}	turn-on energy per pulse			2.3			mJ
E_{off}	turn-off energy per pulse			1.8			mJ
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega$ $L = 100\ \mu\text{H}$; clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$	$T_{VJ} = 125^{\circ}\text{C}$	45			A
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 1200\text{ V}; V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega$; non-repetitive	$T_{VJ} = 125^{\circ}\text{C}$	10			μs
R_{thJC}	thermal resistance junction to case	(per IGBT)			0.95		K/W
R_{thCH}	thermal resistance case to heatsink	(per IGBT)		0.35			K/W

Output Inverter D1 - D6

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 150^{\circ}\text{C}$			1200		V
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			49		A
I_{F80}		$T_C = 80^{\circ}\text{C}$			32		A
V_F	forward voltage	$I_F = 30\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.9		V
I_{RM}	max. reverse recovery current	$V_R = 600\text{ V}$ $di_F/dt = -500\text{ A}/\mu\text{s}$ $I_F = 30\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$	27			A
t_{rr}	reverse recovery time			150			ns
$E_{rec(off)}$	reverse recovery energy			tbd			μJ
R_{thJC}	thermal resistance junction to case	(per diode)			0.9		K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)		0.3			K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Brake Chopper T7

				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V _{CES}	collector emitter voltage	T _{VJ} = 25°C to 150°C			1200	V
V _{GES}	max. DC gate voltage	continuous			±20	V
V _{GEM}	max. transient collector gate voltage	transient			±30	V
I _{C25}	collector current	T _C = 25°C			19	A
I _{C80}		T _C = 80°C			13	A
P _{tot}	total power dissipation	T _C = 25°C			90	W
V _{CE(sat)}	collector emitter saturation voltage	I _C = 15 A; V _{GE} = 15 V	T _{VJ} = 25°C T _{VJ} = 125°C	2.9 3.5	3.4	V V
V _{GE(th)}	gate emitter threshold voltage	I _C = 0.4 mA; V _{GE} = V _{CE}	T _{VJ} = 25°C	4.5	6.5	V
I _{CES}	collector emitter leakage current	V _{CE} = V _{CES} ; V _{GE} = 0 V	T _{VJ} = 25°C T _{VJ} = 125°C	0.8	0.5	mA mA
I _{GES}	gate emitter leakage current	V _{CE} = 0 V; V _{GE} = ±20 V			100	nA
C _{ies}	input capacitance	V _{CE} = 25 V; V _{GE} = 0 V; f = 1 MHz		600		pF
Q _{G(on)}	total gate charge	V _{CE} = 600 V; V _{GE} = 15 V; I _C = 10 A		45		nC
t _{d(on)}	turn-on delay time	} inductive load V _{CE} = 600 V; I _C = 10 A V _{GE} = ±15 V; R _G = 82 Ω	T _{VJ} = 125°C	45		ns
t _r	current rise time			40		ns
t _{d(off)}	turn-off delay time			290		ns
t _f	current fall time			60		ns
E _{on}	turn-on energy per pulse			1.2		mJ
E _{off}	turn-off energy per pulse			1.1		mJ
I _{CM}	reverse bias safe operating area	RBSOA; V _{GE} = ±15 V; R _G = 82 Ω L = 100 μH; clamped induct. load V _{CEmax} = V _{CES} - L _S ·di/dt	T _{VJ} = 125°C	20		A
t _{SC} (SCSOA)	short circuit safe operating area	V _{CE} = 720 V; V _{GE} = ±15 V; R _G = 82 Ω; non-repetitive	T _{VJ} = 125°C	10		μs
R _{thJC}	thermal resistance junction to case	(per IGBT)			1.37	K/W
R _{thCH}	thermal resistance case to heatsink	(per IGBT)		0.45		K/W

Brake Chopper D7

				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_{RRM}	<i>max. repetitive reverse voltage</i>	$T_{VJ} = 150^{\circ}\text{C}$			1200	V
I_{F25}	<i>forward current</i>	$T_C = 25^{\circ}\text{C}$			15	A
I_{F80}		$T_C = 80^{\circ}\text{C}$			10	A
V_F	<i>forward voltage</i>	$I_F = 15\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.0	3.5	V V
I_R	<i>reverse current</i>	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.2	0.06	mA mA
I_{RM}	<i>max. reverse recovery current</i>	$\left. \begin{array}{l} V_R = 600\text{ V}; I_F = 10\text{ A} \\ di_F/dt = -400\text{ A}/\mu\text{s} \end{array} \right\}$	$T_{VJ} = 125^{\circ}\text{C}$	13		A
t_{rr}	<i>reverse recovery time</i>			110		ns
R_{thJC}	<i>thermal resistance junction to case</i>	(per diode)			2.5	K/W
R_{thCH}	<i>thermal resistance case to heatsink</i>	(per diode)		0.05		K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Input Rectifier Bridge D8 - D13

Symbol	Definitions	Conditions	Maximum Ratings	
V_{RRM}	max. repetitive reverse voltage		1600	V
I_{FAV}	average forward current	sine 180°	$T_C = 80^\circ\text{C}$	31 A
I_{DAVM}	max. average DC output current	rectangular; $d = 1/3$; bridge	$T_C = 80^\circ\text{C}$	89 A
I_{FSM}	max. surge forward current	$t = 10\text{ ms}$; sine 50 Hz	$T_C = 25^\circ\text{C}$	320 A
P_{tot}	total power dissipation		$T_C = 25^\circ\text{C}$	80 W

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
V _F	forward voltage	I _F = 30 A	T _{VJ} = 25°C T _{VJ} = 125°C	1.0 1.1	V V
I _R	reverse current	V _R = V _{RRM}	T _{VJ} = 25°C T _{VJ} = 125°C	0.4	0.02 mA mA
R _{thJC}	thermal resistance junction to case	(per diode)	T _{VJ} = 25°C		1.4 K/W
R _{thCH}	thermal resistance case to heatsink	(per diode)		0.45	K/W

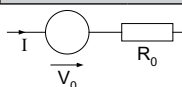
Temperature Sensor NTC

					Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	Unit	
R ₂₅	resistance	T _c = 25°C	4.45	4.7	5.0	kΩ	
B _{25/85}				3510		K	

Module

			Ratings			
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
T _{VJ}	operating temperature		-40		125	°C
T _{VJM}	max. virtual junction temperature				150	°C
T _{stg}	storage temperature		-40		125	°C
V _{ISOL}	isolation voltage	I _{ISOL} ≤ 1 mA; 50/60 Hz			2500	V~
M _d	mounting torque	(M4)	2.0		2.2	Nm
d _S	creep distance on surface		12.7			mm
d _A	strike distance through air		12.7			mm
Weight				40		g

Equivalent Circuits for Simulation

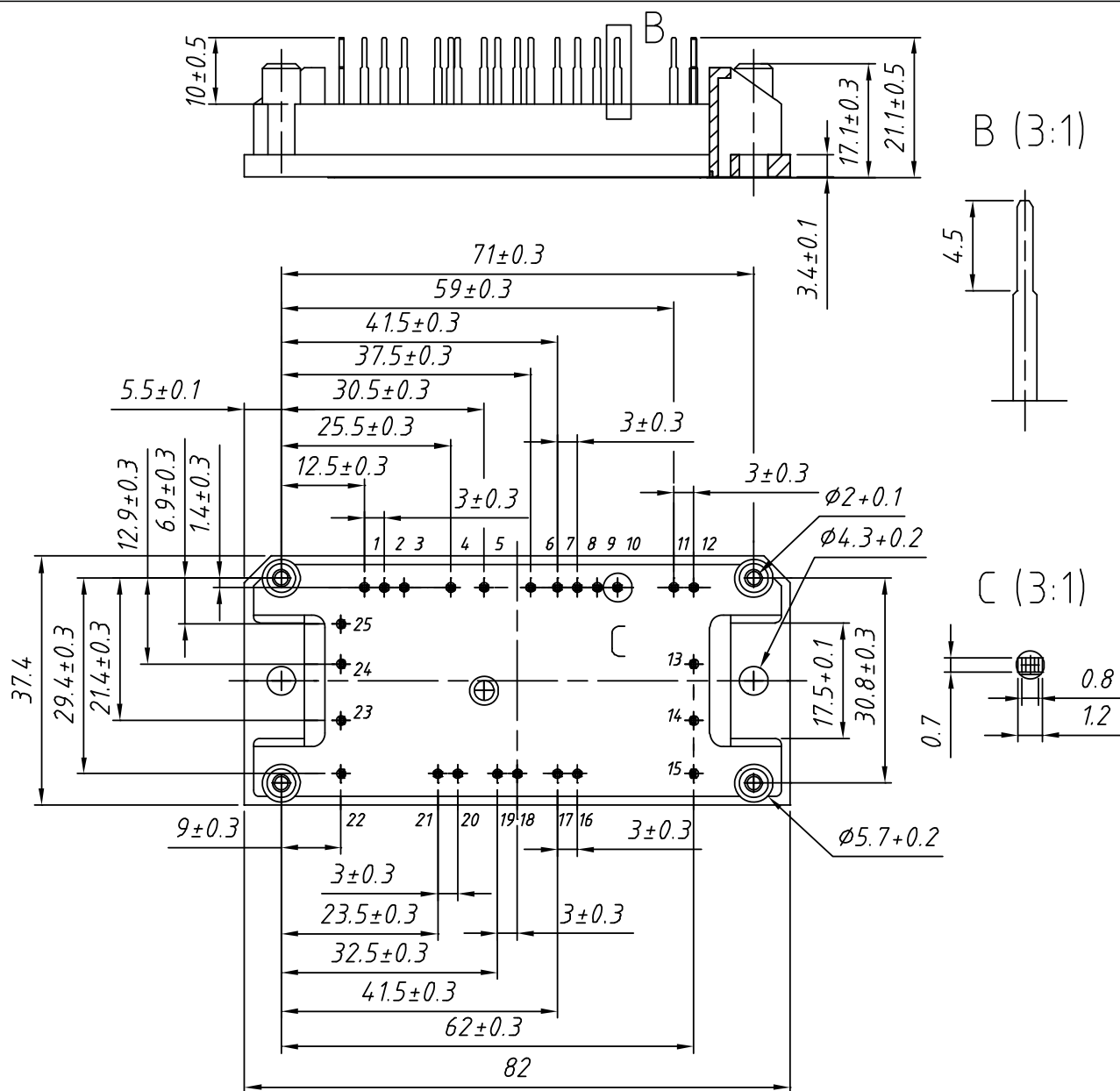


Symbol	Definitions	Conditions	min.	Ratings		Unit
				typ.	max.	
V_0 R_0	rectifier diode	D8 - D13	$T_{VJ} = 125^\circ\text{C}$	0.90 9		V m Ω
V_0 R_0	IGBT	T1 - T6	$T_{VJ} = 125^\circ\text{C}$	tbd tbd		V m Ω
V_0 R_0	free wheeling diode	D1 - D6	$T_{VJ} = 125^\circ\text{C}$	1.5 14		V m Ω
V_0 R_0	IGBT	T7	$T_{VJ} = 125^\circ\text{C}$	1.5 120		V m Ω
V_0 R_0	free wheeling diode	D7	$T_{VJ} = 125^\circ\text{C}$	1.46 63		V m Ω

$T_C = 25^\circ\text{C}$ unless otherwise stated

Outline Drawing

Dimensions in mm (1 mm = 0.0394")



Product Marking

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MUBW 30-12A6K	MUBW30-12A6K	Box	10	499 854

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